

CLAIM AMENDMENT

1. (Original) A quantum device comprising a pair of dopant atoms located in an otherwise electrically inert solid substrate in which it is possible to ionise the dopant atoms; wherein the two dopants produce a double-well electric potential and a charge qubit is realised by the location of one or more electrons or holes within this potential.
2. (Original) A quantum device according to claim 1, wherein the substrate is silicon, the dopant is phosphorus and ionisation of one of the donor electrons creates a $P-P^+$ system.
3. (Original) A quantum device according to claim 2, wherein a charge qubit is formed by the location of a single electron in one or other well of the double-well potential.
4. (Original) A quantum device according to claim 2, wherein the charge qubit is formed the lowest symmetric or antisymmetric molecular states.
5. (Original) A quantum device according to claim 2, wherein the spacing between the P atoms is up to 200nm.
6. (Original) A quantum device according to claim 5, wherein the spacing between the P atoms is in the range 20 to 100nm.
7. (Original) A quantum device according to claim 2, wherein the two P atoms are buried up to 200nm below the surface of the device.
8. (Original) A quantum device according to claim 7, wherein the two P atoms are buried in the range 5 to 50nm.
9. (Original) A quantum device according to claim 2, wherein the silicon substrate is coated with an insulating layer to isolate the donor electrons from any surface electrodes.

10. (Original) A quantum device according to claim 9, wherein the insulating layer is SiO₂.
11. (Original) A quantum device according to claim 2, wherein gate electrodes are placed on the surface of the substrate above the donor atoms to allow for external control of the charge wavefunctions.
12. (Original) A quantum device according to claim 11, wherein a first gate is located over the potential barrier, between the two wells, to control the barrier height, this gate is known as the 'barrier' gate or B-gate.
13. (Original) A quantum device according to claim 12, wherein a second gate, or more than one second gate, is provided to control the relative shapes and sizes of the two wells, this gate is known as the 'potential off-set', 'symmetry' or S-gate.
14. (Original) A quantum device according to claim 13, wherein suitable biasing of the first and second gates allows one qubit logic operations to be performed.
15. (Original) A quantum device according to claim 11, wherein one or more charge detection devices are provided on the surface of the substrate for qubit readout and to confirm initialization of qubits.
16. (Original) A quantum device according to claim 15, wherein the charge detection device is a sensitive field-effect transistor, or a single electron transistor (SET).
17. (Currently Amended) A quantum device according to claim 2 ~~any preceding claim~~, wherein the configuration comprising two dopant atoms, surface gates and surface charge detection devices is repeated many times on a single silicon chip, allowing for scale-up to a many qubit processor.

18. (Original) A quantum device according to claim 17, wherein the device is cooled to ensure that the donors are not thermally ionised and to minimise coupling of the charge qubits to the environment.
19. (Original) A quantum device according to claim 18, wherein it is cooled to 4K or below.
20. (Original) A quantum device comprising two pairs of dopant atoms, each located in a solid substrate such that two double-well potentials are created; and two charge qubits are formed by the location of one or more electrons within the double-well potentials; where, one or more gates above the substrate control electron tunneling between the two qubits; and where, by suitable biasing of these and other gate electrodes, two-qubit logic operations may be performed.
21. (Original) A quantum device comprising two pairs of dopant atoms, each located in a solid substrate such that two double-well potentials are created; and two charge qubits are formed by the location of one or more electrons within the double-well potentials; and where, one or more gates above the substrate controls the Coulomb interaction between the two qubits; and where, by suitable biasing of these and other gate electrodes, two-qubit logic operations may be performed.
22. (Original) A quantum device comprising more than one of the devices comprising two pairs of donor atoms, arranged adjacent each other, and having gates to enable interaction between each adjacent pair.
23. (Currently Amended) A method of reading out the logic state of a qubit from a quantum device having a single electron transistor (SET) having an S-gate ~~according to any preceding claim~~, comprising the steps of:

- (i) Biasing the S-gate to a non-zero value to define a known relaxed state for which the SET has been previously calibrated;
- (ii) Turning on the SET;
- (iii) Waiting for a period of time for the system to relax to the relaxed state;
- (iv) Monitoring SET current during the waiting period to determine whether a change of state occurs, or not;
- (v) Inferring the state before step (i) from the behaviour of the SET current monitored during step (iv).

24. (Currently Amended) A method of initializing the logic state of each qubit in a quantum device having a single electron transistor having an S-gate ~~according to any one of claims 1 to 22~~, comprising the steps of:

- (i) Biasing the S-gate to a non-zero value to define a known relaxed state;
- (ii) Waiting for a period of time for the system to relax to the relaxed state.

25. (Original) A method of using a quantum device according to any one of claims 1 to 22 to perform quantum computations, comprising typical steps which include:

- (i) Initializing each qubit in the quantum device;
- (ii) Using a suitable quantum algorithm to carry out one-qubit and two-qubit operations on the qubits in the device via an appropriately timed sequence of control gate biasing;
- (iii) Reading out the logical states of the qubits.

26. (Currently Amendment) A method of making a quantum device ~~a quantum device according to any one of claims 1 to 22~~, comprising the steps of:

- (i) creating a resist mask for implantation of an array of one or more pairs of dopant atoms into a semiconductor substrate;
- (ii) implanting one dopant ion through each hole in the mask to form an array of buried-atom qubits;
- (iii) fabricating conducting electrodes above each implanted pair of donor atoms to serve as a B gate, an S gate and a SET;

- (iv) annealing the device to a temperature sufficient to remove implant lattice damage and activate the dopant – this step may occur either immediately before or after step (iii);
- (v) pre-initializing each pair of donor atoms to remove one of the electrons.

27. (Currently Amended) A method of making a quantum device ~~according to any one of claims 1 to 22~~, comprising the steps of:

- (i) passivating a clean semiconductor surface;
- (ii) patterning the passivated surface to open an array of holes;
- (iii) exposing the resulting surface to donor atoms, perhaps in the form of dopant-bearing molecules;
- (iv) overgrowing the dopant atom array with further layers of the semiconductor and annealing if necessary;
- (v) coating the surface with an insulating layer if necessary;
- (vi) fabricating conducting electrodes above each implanted pair of donor atoms to serve as a B gate, an S gate and a SET;
- (vii) pre-initializing each pair of donor atoms to remove one of the electrons.

Respectfully submitted,

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